

1、Description

BTA204 series triacs, with high ability to withstand the shock loading of large current, provide high dv/dt rate with strong resistance to electromagnetic interface. With high commutation performances, 3 quadrants products especially recommended for use on inductive load.

2、Applications

- Motor control
- Industrial and domestic lighting
- Heating
- Static switching

3、Features

- Blocking voltage to 800 V
- On-state RMS current to 4 A
- Ultra low gate trigger current
- Low cost package.

4、Pinning information

PIN	Description	Simplified outline	Symbol
1	main terminal 1(T1)	 TO-252	
2	main terminal 2(T2)		
3	gate (G)		
tab	main terminal T2		

5、Quick reference data

SYMBOL	PARAMETER	MAX	UNIT
V_{DRM} V_{RRM}	Repetitive peak off-state voltages	800	V
$I_{T(RMS)}$	RMS on-state current	4	A
I_{TSM}	Non-repetitive peak on-state current	40	A

6、Thermal characteristics

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
$R_{th(j-c)}$	junction to case(AC)	in free air	-	2.8	-	°C /W

7、Limiting value

Limiting values in accordance with the Maximum System(IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
V_{DRM} V_{RRM}	Repetitive peak off-state voltages		-	800	V
$I_{T(RMS)}$	RMS on-state current	Full Cycle Sine Wave 50 to 60 Hz (TC = 86°C)	-	4	A
I_{TSM}	Non-repetitive peak Surge current	One Full cycle, 50 Hz	-	40	A
I^2t	I^2t for fusing	$t = 10\text{ms}$	-	8	A^2s
dI/dt	Critical rate of rise of on-state current	$I_G=2XI_{GT}$		50	$\text{A}/\mu\text{s}$
I_{GM}	Peak gate current		-	4	A
P_{GM}	Peak gate power		-	5	W
$P_{G(AV)}$	Average gate power		-	1	W
T_{stg}	Storage temperature		-40	150	°C
T_j	Operating junction temperature		-40	125	°C

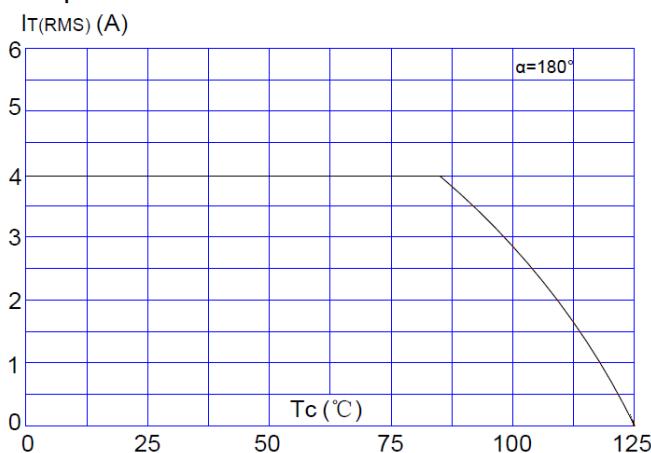
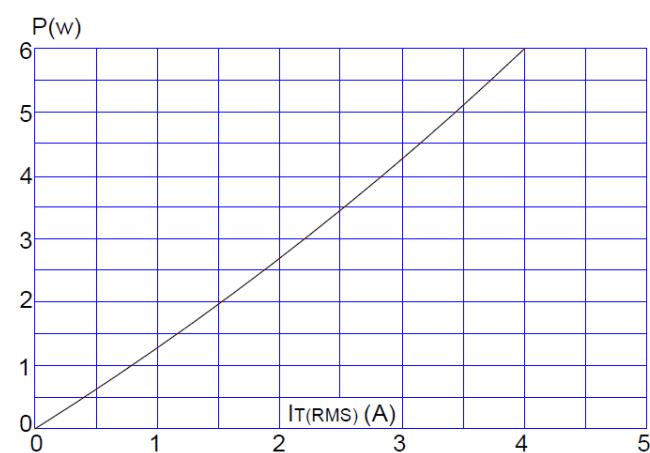
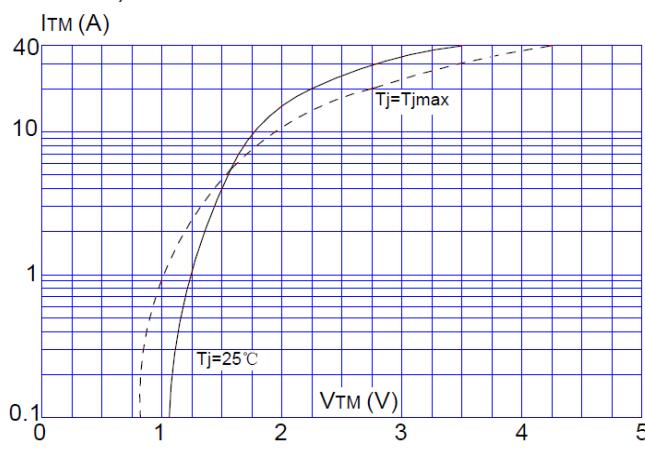
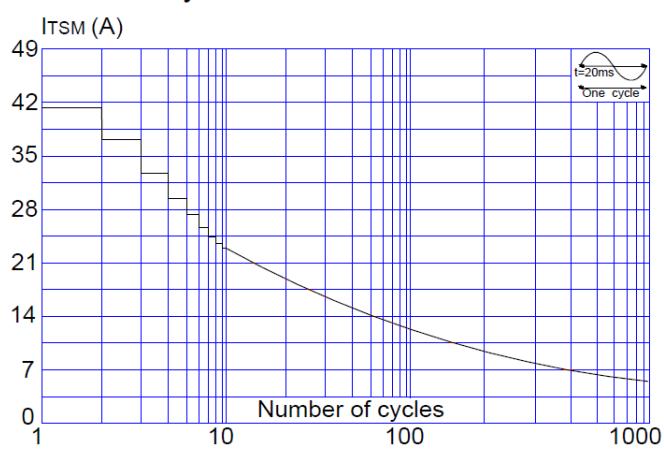
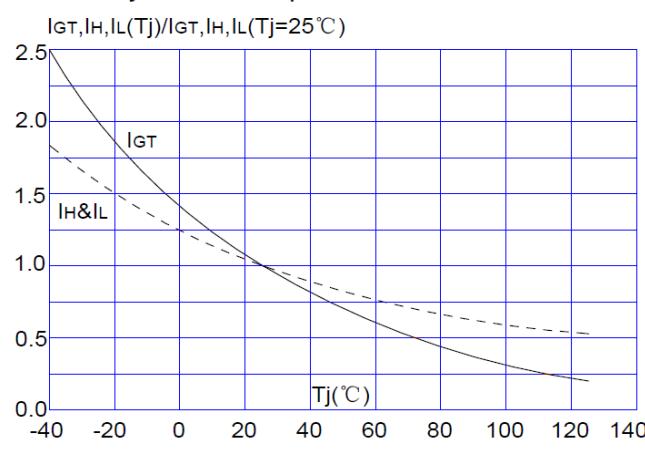
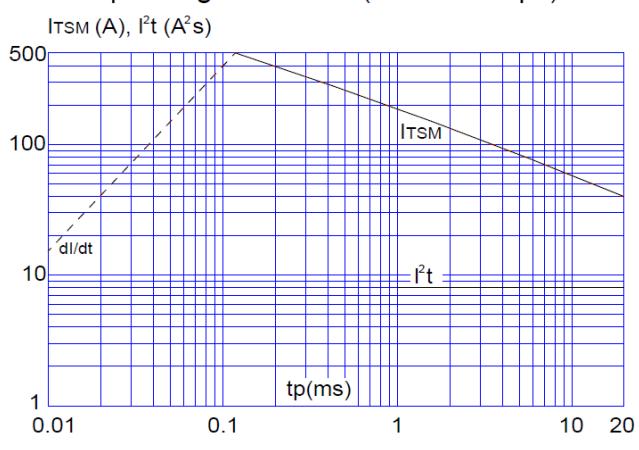
8、Characteristics

$T_J = 25^\circ\text{C}$ unless otherwise stated

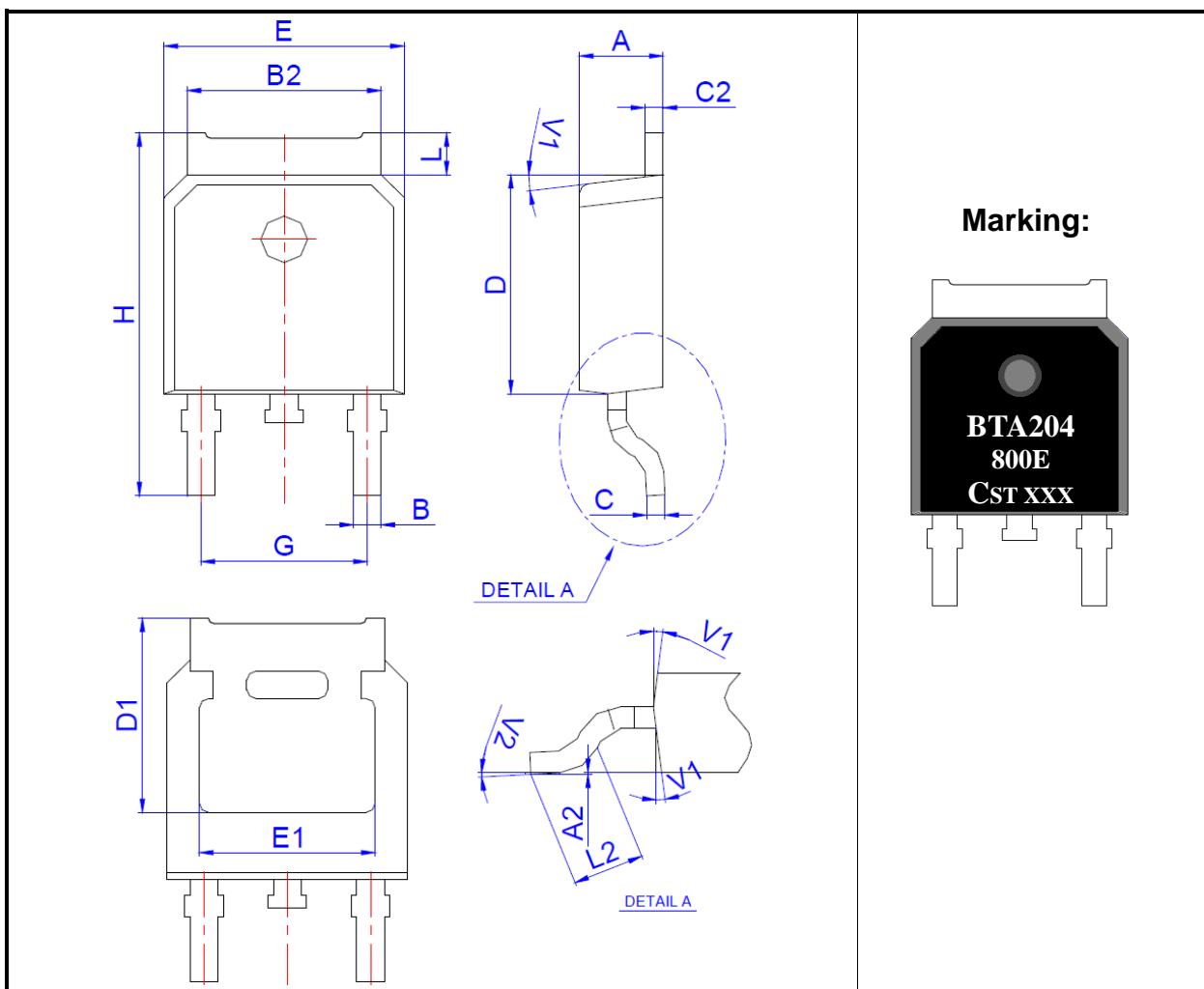
SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
Static characteristics						
I_{GT}	Gate trigger current	$V_D = 12 \text{ V}; RL = 33\Omega$ T2+ G+ T2+ G- T2- G-	-	-	10	mA
I_L	Latching current	$I_G = 1.2XI_{GT}$ T2+ G+ T2+ G- T2- G-	-	-	20	mA
I_H	Holding current	$IT = 100\text{mA}$	-	-	15	mA
V_{TM}	On-state voltage	$I_{TM} = 5.5\text{A}$ tp=380μs	-	-	1.55	V
V_{GT}	Gate trigger voltage	$V_D = 12 \text{ V}; RL = 33\Omega$ T2+ G+ T2+ G- T2- G-	-	-	1.5	V
V_{GD}	Gate Non-Trigger Voltage	$VD = V_{DRM}$ $T_J = 125^\circ\text{C}$ $RL = 3.3\text{K}\Omega$ T2+ G+, T2+ G-, T2- G-	0.2	-	-	V
I_{DRM} I_{RRM}	$V_D = V_{DRM}$ $V_R = V_{RRM}$	$T_J = 25^\circ\text{C}$ $T_J = 125^\circ\text{C}$	-	-	10	uA
Dynamic Characteristics						
dV/dt	Critical rate of rise of off-state voltage	$V_D = 2/3V_{DRM}$ Gate Open $T_J = 125^\circ\text{C}$	100	-	-	$\text{V}/\mu\text{s}$
$(dV/dt)c$	Critical rate of change of commutating voltage	$(dI/dt)c = 1.8\text{A}/\text{ms}$ $T_J = 125^\circ\text{C}$	1	-	-	$\text{V}/\mu\text{s}$

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9. Electrical Characteristics Curve

FIG.1: RMS on-state current versus case temperature**FIG.2:** Maximum power dissipation versus RMS on-state current**FIG.3:** On-state characteristics (maximum values)**FIG.4:** Surge peak on-state current versus number of cycles**FIG.5:** Relative variations of gate trigger current, holding current and latching current versus junction temperature**FIG.6:** Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 20\text{ms}$ and corresponding value of I^2t ($dl/dt < 50\text{A}/\mu\text{s}$)

10、Package outline(TO-252)



DIM	Inches			Milimeters		
	Min	Type	Max	Min	Type	Max
A	0.083	-	0.098	2.10	-	2.50
A2	0.001	-	0.009	0.03	-	0.23
B	0.026	-	0.034	0.66	-	0.86
B2	0.202	-	0.216	5.18	-	5.48
C	0.016	-	0.024	0.40	-	0.60
C2	0.017	-	0.023	0.44	-	0.58
D	0.232	-	0.248	5.90	-	6.30
D1		0.209REF			5.30REF	
E	0.252	-	0.268	6.40	-	6.80
E1	0.182			4.63		
G	0.176	-	0.184	4.47	-	4.67
H	0.374	-	0.421	9.50	-	10.70
L	0.043	-	0.048	1.09	-	1.21
L2	0.053	-	0.065	1.35	-	1.65
V1		7°			7°	
V2	0°		6°	0°		6°

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